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November 2013

FDP18N50 / FDPF18N50 / FDPF18N50T N-Channel UniFETTM MOSFET

500 V, 18 A, 265 mΩ

Features

- $R_{DS(on)}$ = 220 $m\Omega$ (Typ.) @ V_{GS} = 10 V, I_D = 9 A
- Low Gate Charge (Typ. 45 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested

Applications

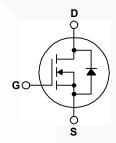
- LCD/LED/PDP TV
- Lighting
- · Uninterruptible Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDP18N50	FDPF18N50 / FDPF18N50T	Unit
V _{DSS}	Drain-Source Voltage		500		V
I _D	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	18 10.8	18 * 10.8 *	A A
I _{DM}	Drain Current	- Pulsed (Note 1)	72	72 *	Α
V _{GSS}	Gate-Source voltage		±30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		945		mJ
I _{AR}	Avalanche Current (Note 1)		18		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		23.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P _D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C	235 1.88	38.5 0.3	W W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum Lead Temperature 1/8" from Case for 5 Seconds		30	°C	

^{*} Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP18N50	FDPF18N50 / FDPF18N50T	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.53	3.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP18N50	FDP18N50	TO-220	Tube	N/A	N/A	50 units
FDPF18N50	FDPF18N50	TO-220F	Tube	N/A	N/A	50 units
FDPF18N50T	FDPF18N50T	TO-220F	Tube	N/A	N/A	50 units

$\textbf{Electrical Characteristics} \quad \textbf{T}_{C} = 25^{\circ} \text{C unless otherwise noted}.$

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	cteristics				*	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	500			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V V _{DS} = 400 V, T _C = 125°C			1 10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 9 A		0.220	0.265	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 9 A		25		S
Dynamic C	Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		2200	2860	pF
C _{oss}	Output Capacitance	f = 1 MHz		330	430	pF
C _{rss}	Reverse Transfer Capacitance			25	40	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 18 A,		55	120	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_G = 25 Ω		165	340	ns
t _{d(off)}	Turn-Off Delay Time		/	95	200	ns
t _f	Turn-Off Fall Time	(Note 4)	/	90	190	ns
Qg	Total Gate Charge	V _{DS} = 400 V, I _D = 18 A,		45	60	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		12.5		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		19		nC
Drain-Sou	rce Diode Characteristics and Maximur	m Ratings				
Maximum Continuous Drain-Source Diode Forward Current					18	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				72	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 18 A			1.4	٧
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = 18 \text{ A,}$ $dI_{F}/dt = 100 \text{ A/}\mu\text{s}$		500		ns
Q _{rr}	Reverse Recovery Charge			5.4		μС

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 5.2 mH, I_{AS} = 18 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
- 3. $I_{SD} \le$ 18 A, di/dt \le 200 A/ μ s, $V_{DD} \le$ BV $_{DSS}$, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

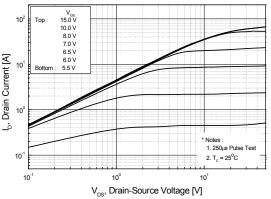


Figure 2. Transfer Characteristics

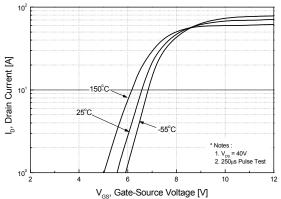
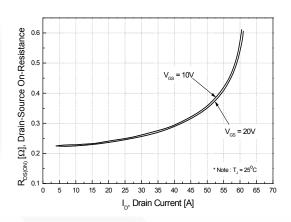


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



l_{DR}, Reverse Drain Current [A] 1. V_{GS} = 0V 2. 250μs Pulse Test 10⁰ – 0.4 0.6 0.8 1.2 1.4 1.6 2.0 2.2 V_{SD}, Source-Drain voltage [V]

Figure 5. Capacitance Characteristics

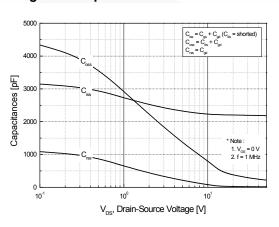
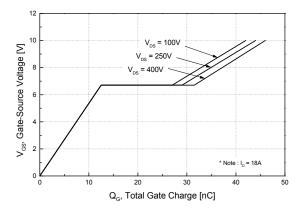


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

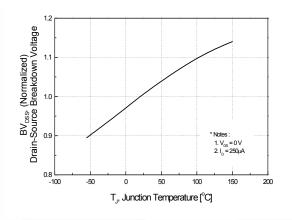


Figure 8. On-Resistance Variation vs. Temperature

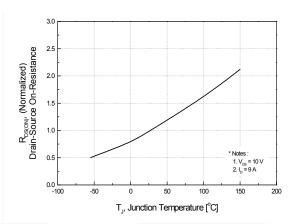
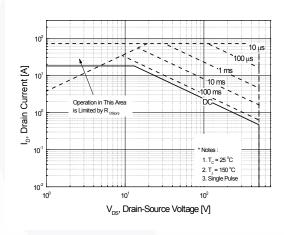


Figure 9-1. Maximum Safe Operating Area - FDP18N50





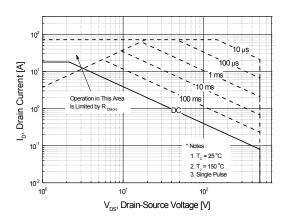
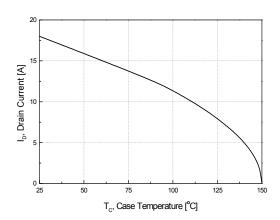


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP18N50

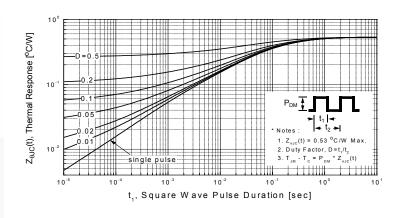
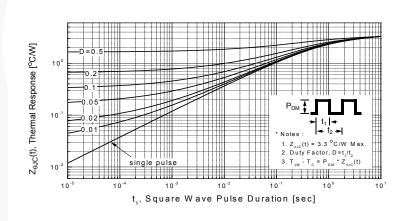


Figure 11-2. Transient Thermal Response Curve - FDPF18N50 / FDPF18N50T



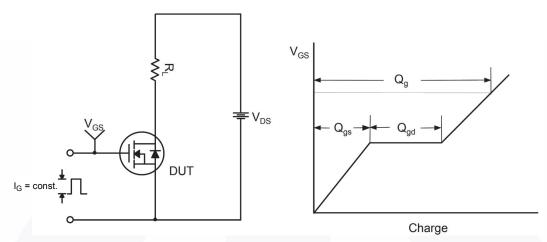


Figure 12. Gate Charge Test Circuit & Waveform

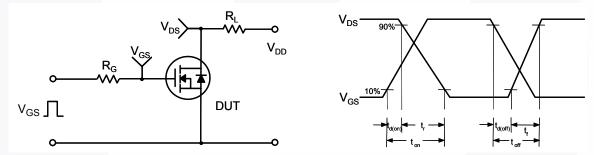


Figure 13. Resistive Switching Test Circuit & Waveforms

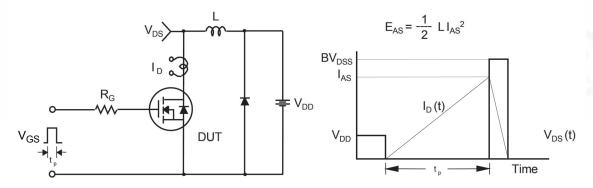


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

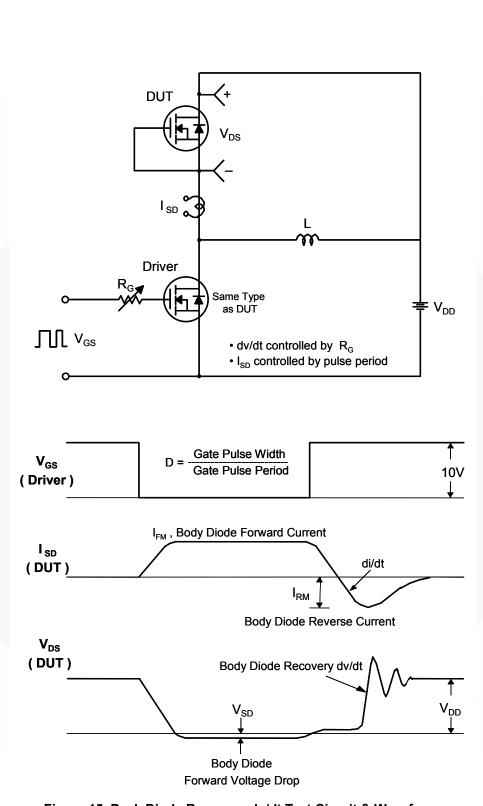


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

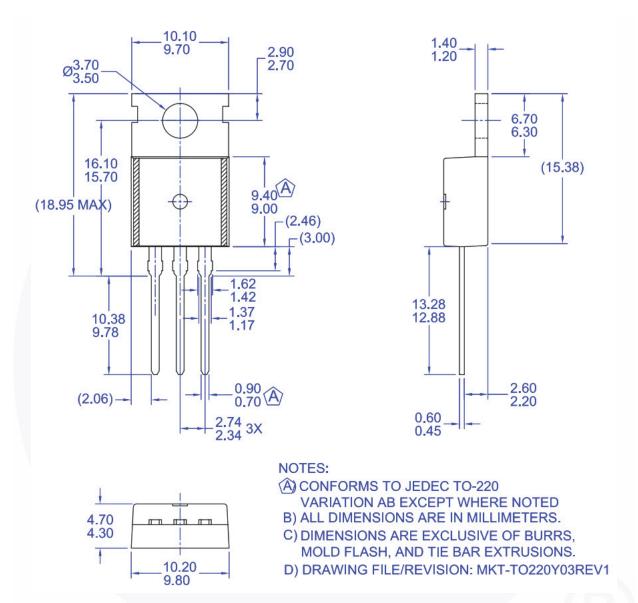


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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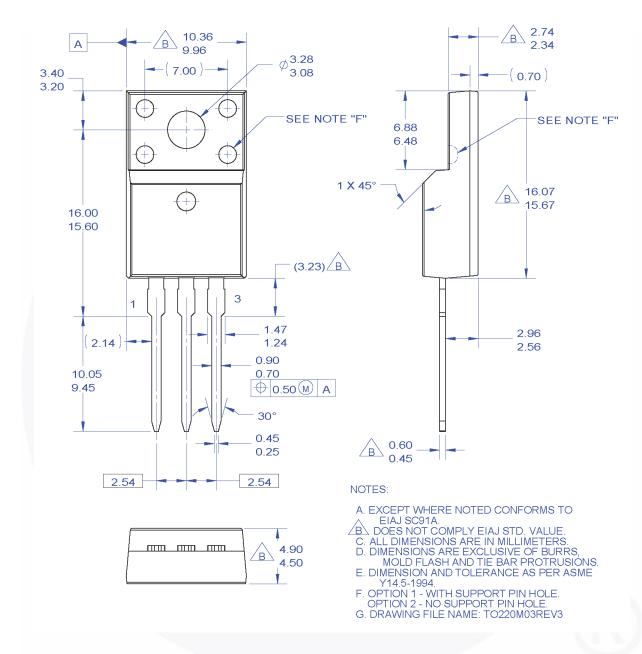


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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